

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TPV3100** is a Class AB Common Device Designed for Television Band IV & V Applications.

FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting
- Internal Matching

MAXIMUM RATINGS

I_C	12 A
V_{CC}	65 V
P_{DISS}	215 W @ T _C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +200 °C
q_{JC}	0.80 °C/W

PACKAGE STYLE .450 BAL FLG.(A)

	MINIMUM Inches/mm	MAXIMUM Inches/mm		MINIMUM Inches/mm	MAXIMUM Inches/mm
		055/1.40	K	002/0.05	006/0.15
B	120/3.05	130/3.30	L	055/1.40	065/1.65
C		785/19.94	M	080/2.03	095/2.41
D	455/11.56	465/11.81	N		195/4.95
E	130/3.30		P	455/11.56	468/11.89
F	230/5.84				
G	120/3.05				
H	838/21.28	850/21.59			
I	1095/27.81	1105/28.07			
J	525/13.34	535/13.59			

1 = Collector 2 = Base
3 = Emitter

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 20 mA			65			V
BV_{CER}	I _C = 10 mA	R _{BE} = 75 Ω		30			V
BV_{EBO}	I _E = 10 mA			4.0			V
I_{CER}	V _{CE} = 28 V	R _{BE} = 75 Ω				10	mA
h_{FE}	V _{CE} = 10 V	I _C = 2.0 A		30		120	---
P_{1dB}	V _{CE} = 28 V	I _{CQ} = 2X50 mA	Fo = 860 MHz	100			W
P_g	V _{CE} = 28 V	I _{CQ} = 2X50 mA	Fo = 860 MHz	8.5	9.5		dB